



Packaging Trends for Millimeter-Wave Radar and Communication Systems

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Agenda

1

Introduction

2

Millimeter-Wave System Integration

3

2D Embedded Wafer Level BGA (eWLB)

4

3D System Integration Applying eWLB

5

Summary

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Global Trends



Every year the world population increases by about 80 million people



Demand for electricity is projected to rise by 50% until 2030



Mobile life will be major driver of growth for the next decade

Rapid changes require innovative solutions

Trends in Communication and Radar Systems



- High-speed wireless communication
- **Frequency spectrum up to 100 GHz** (6 GHz, 28 GHz, 38 GHz, 60 GHz, 73 GHz, ...)



- Internet connectivity for everyday items
- **High-speed wireless communication and environment sensing systems** (24 GHz, 61 GHz, 122 GHz, ...)



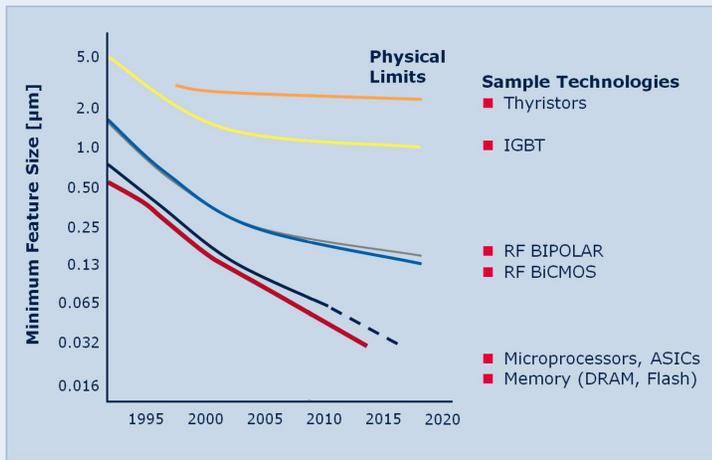
- Making the car part of the internet
- High-speed wireline and wireless communication
- **Millimeter-wave radar for safety and sensing** (24 GHz, 77 GHz)

More Moore is Getting Out of Steam

Miniaturization More Moore reaches limits

By shrinking of ICs

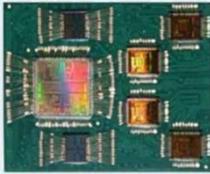
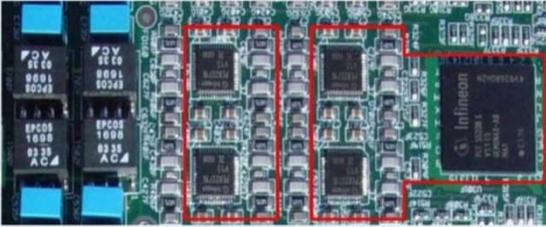
- Better RF performance/higher speed
- Lower energy consumption
- Smaller size
- Lower cost



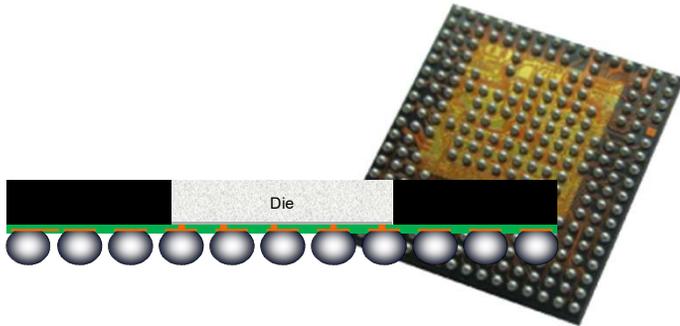
More Moore getting out of steam

Functional diversification More than Moore

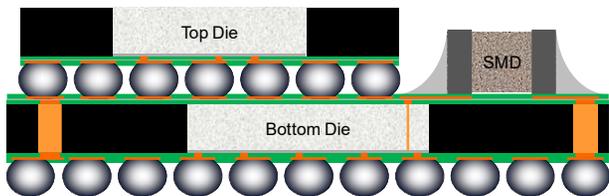
- Trend toward functional diversification
- The assembly and packaging role is expanding to include system level integration functions
- System-in-Package (SiP) and heterogeneous integration



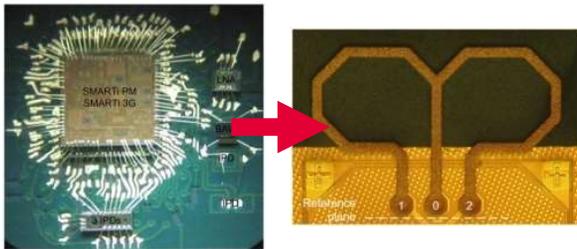
Developments for System-in-Package



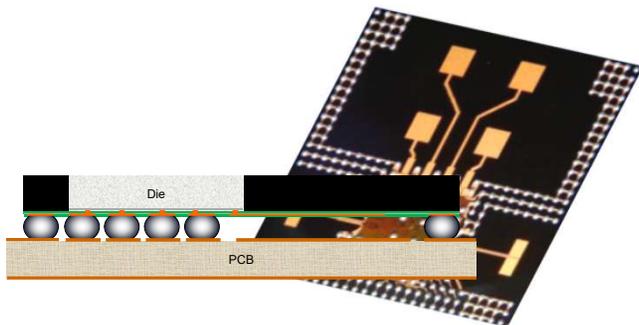
- High I/O count
- Wafer level packaging (WLP)



- 3D integration
- Package-on-Package (TSV, TEV)



- Passive integration
- Coils, transformers, power dividers



- Antenna integration

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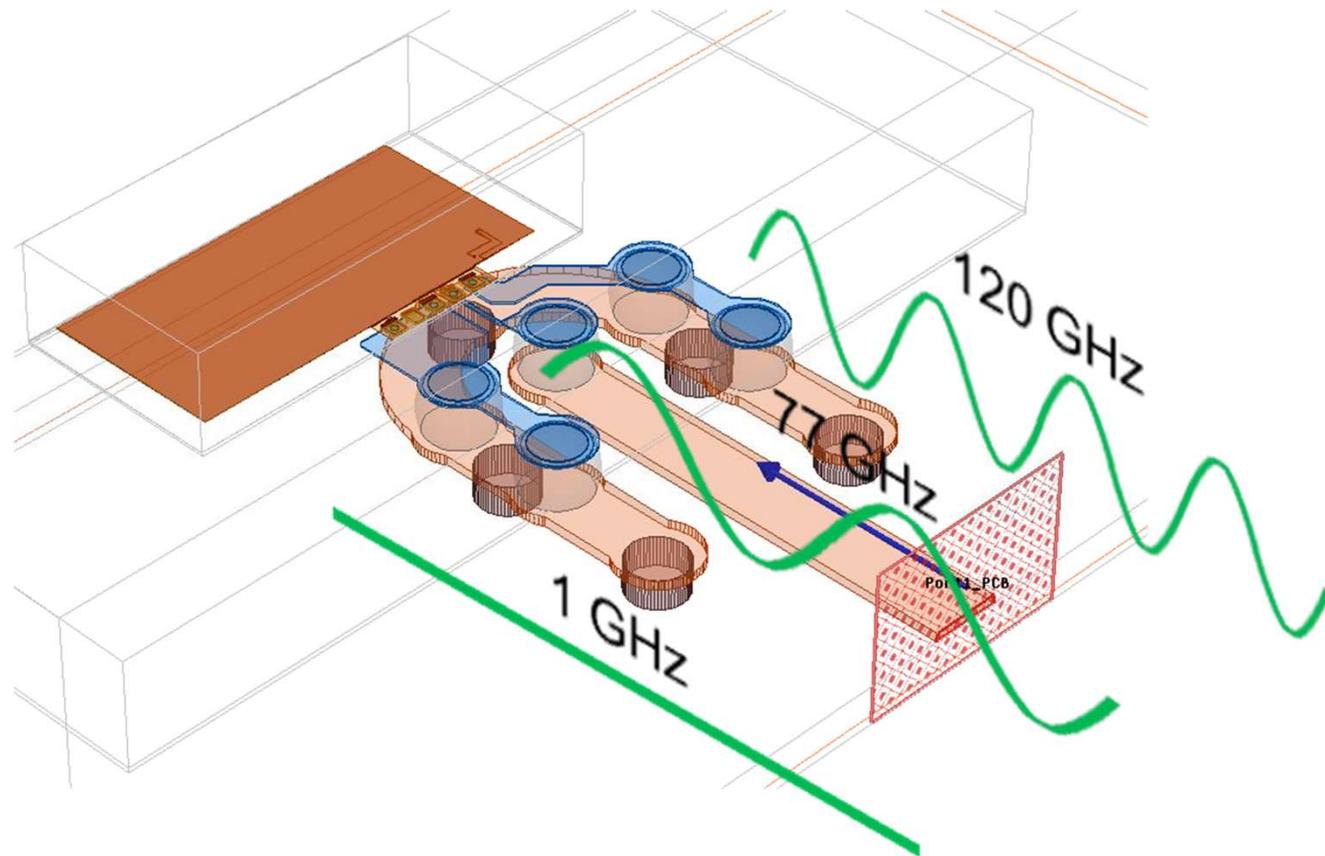
Challenges at Millimeter-Wave Frequencies

- Size of a package $\sim \lambda$
- Parasitic wave effects
 - Impedance mismatch and signal reflections
 - Crosstalk
 - EM radiation
- Increased impact of manufacturing tolerances
 - Large pitches
 - Coarse metal pattern resolution

What is “high frequency”?

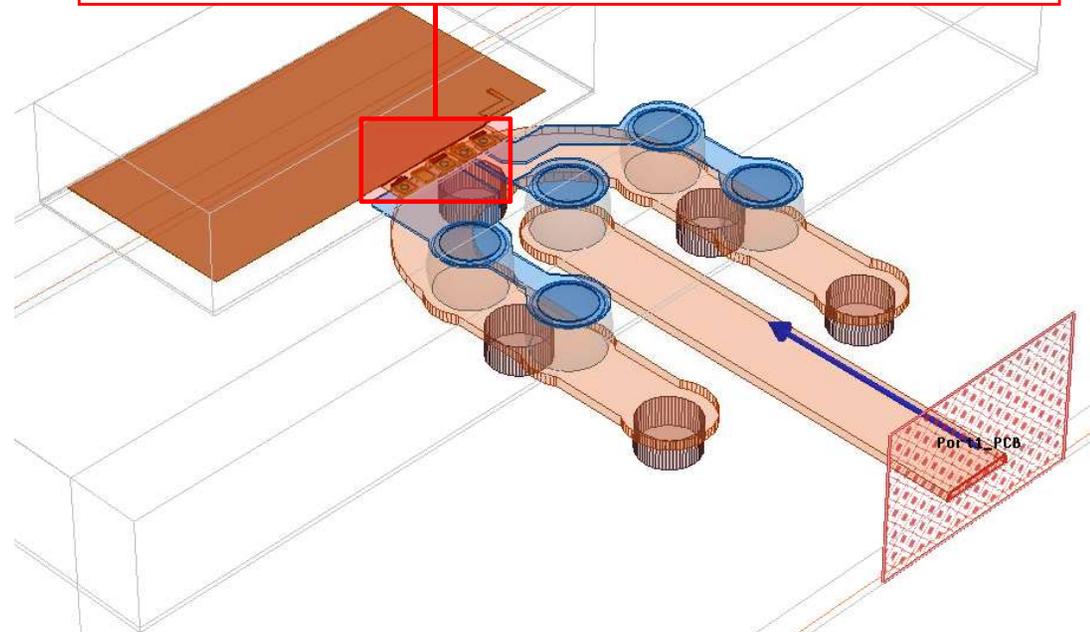
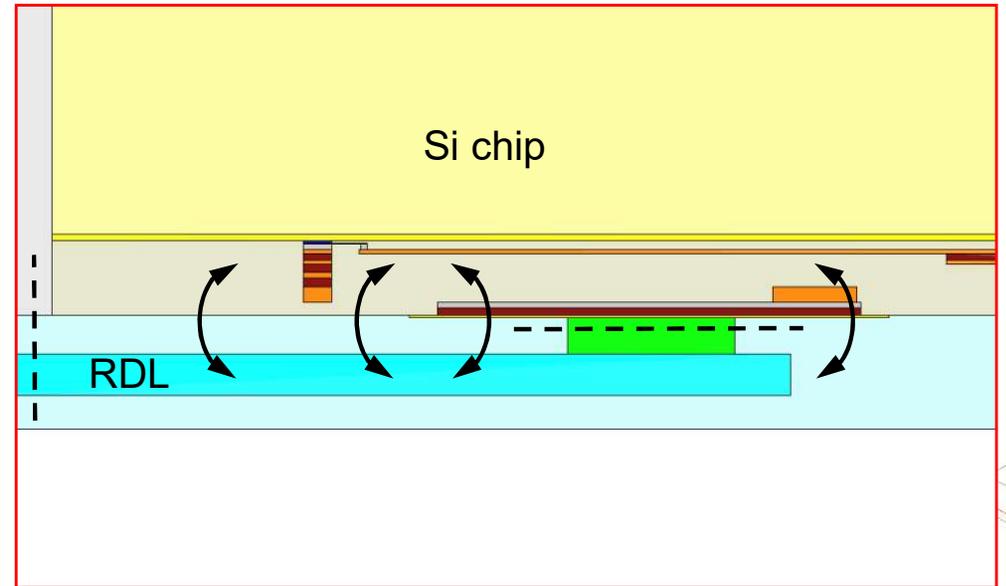
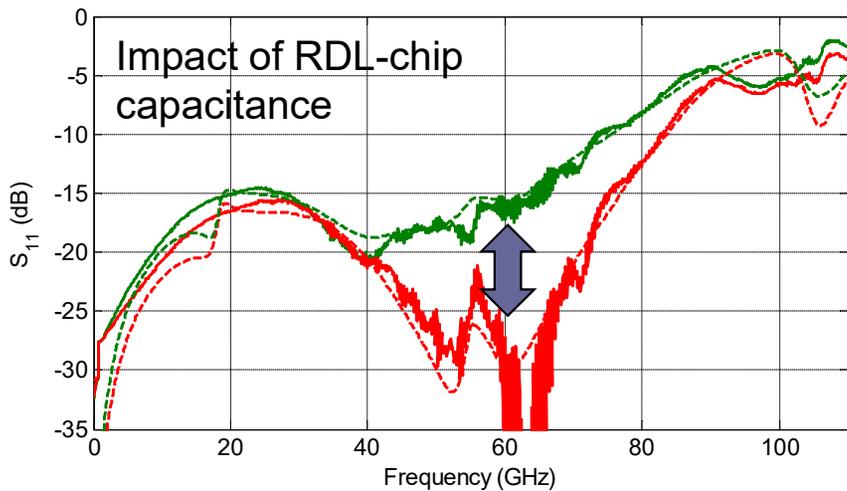
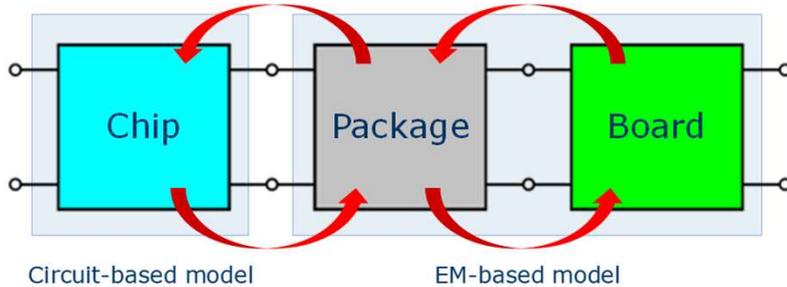
Wavelength \approx geometrical dimension

Frequency	λ ($\epsilon_r = 3.0$)	$\lambda/4$ ($\epsilon_r = 3.0$)
10 GHz	17.3 mm	4.3 mm
24 GHz	7.2 mm	1.8 mm
60 GHz	2.9 mm	0.72 mm
77 GHz	2.3 mm	0.56 mm
120 GHz	1.4 mm	0.36 mm



Chip-Package Interactions

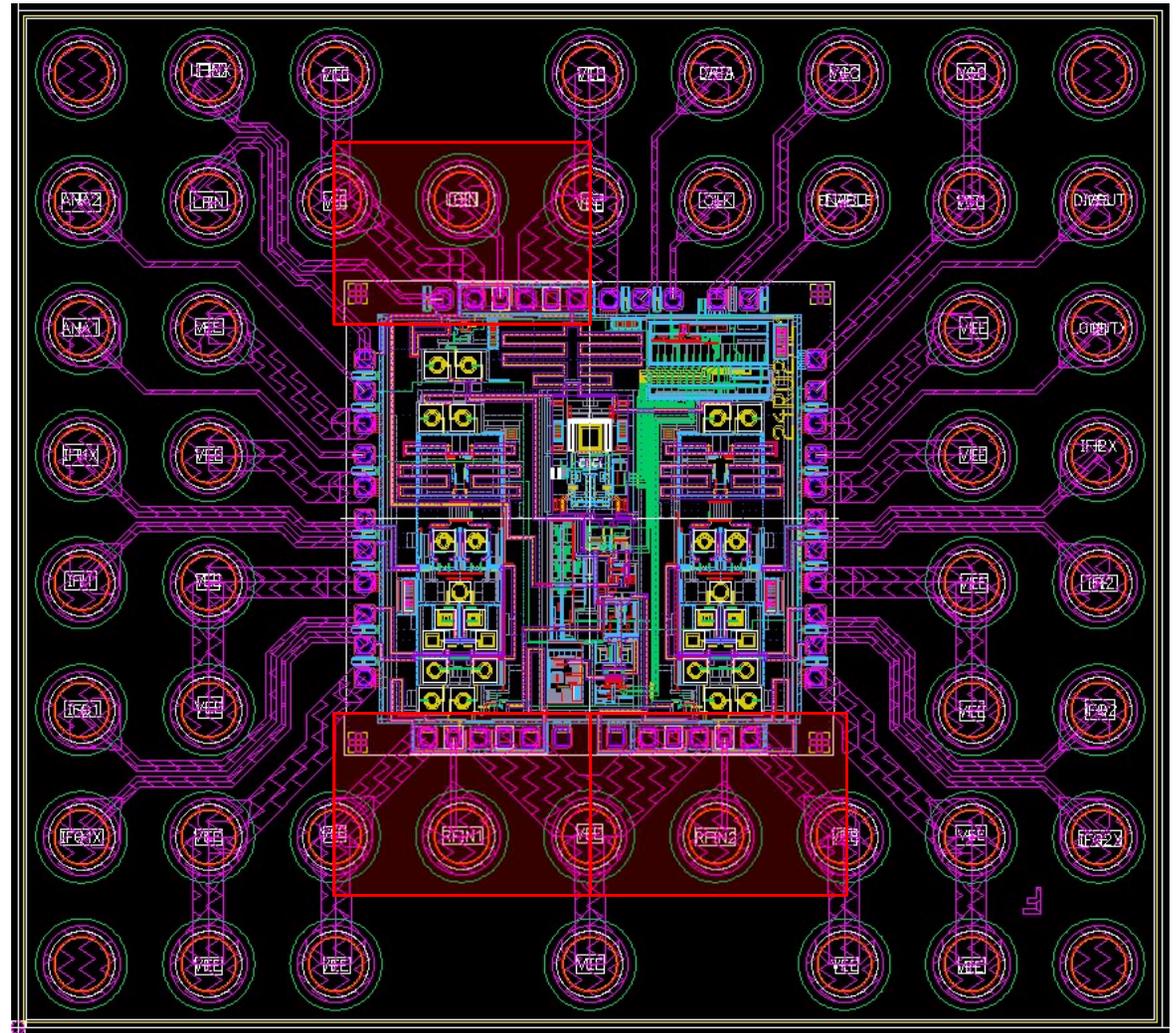
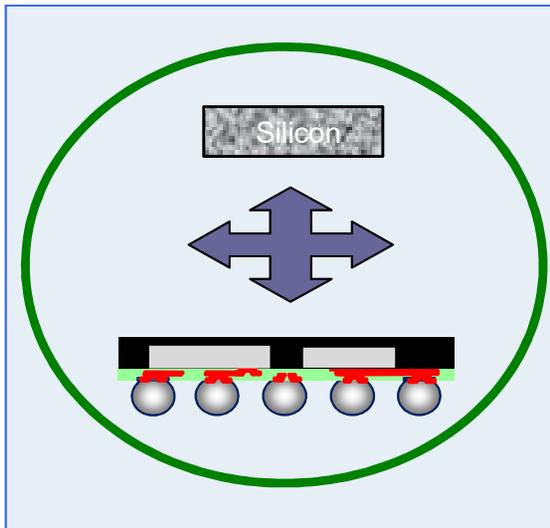
- Strong chip-package EM interactions limit the use of standard modeling approaches based on the principle of partitioning and cascading



- New methodologies are needed for coherent chip-package-board co-design

Concurrent Editing

- Implementation of physical layout of both chip and package takes place in one design environment
- Successfully applied for development of Infineon mm-wave products



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Success Story of eWLB

2006
Introduction of eWLB

a) Fan-Out area (mold), Chip, Redistribution layer (RDL)

b) Chip, RDL

2008
77 GHz SiGe mixer in eWLB

2007
Low-loss transmission lines and high-Q inductors in eWLB
EPTC 2007 Outstanding Paper Award

2012
77 GHz SiGe TRX with integrated antennas in eWLB
ECTC 2012 Outstanding Paper Award

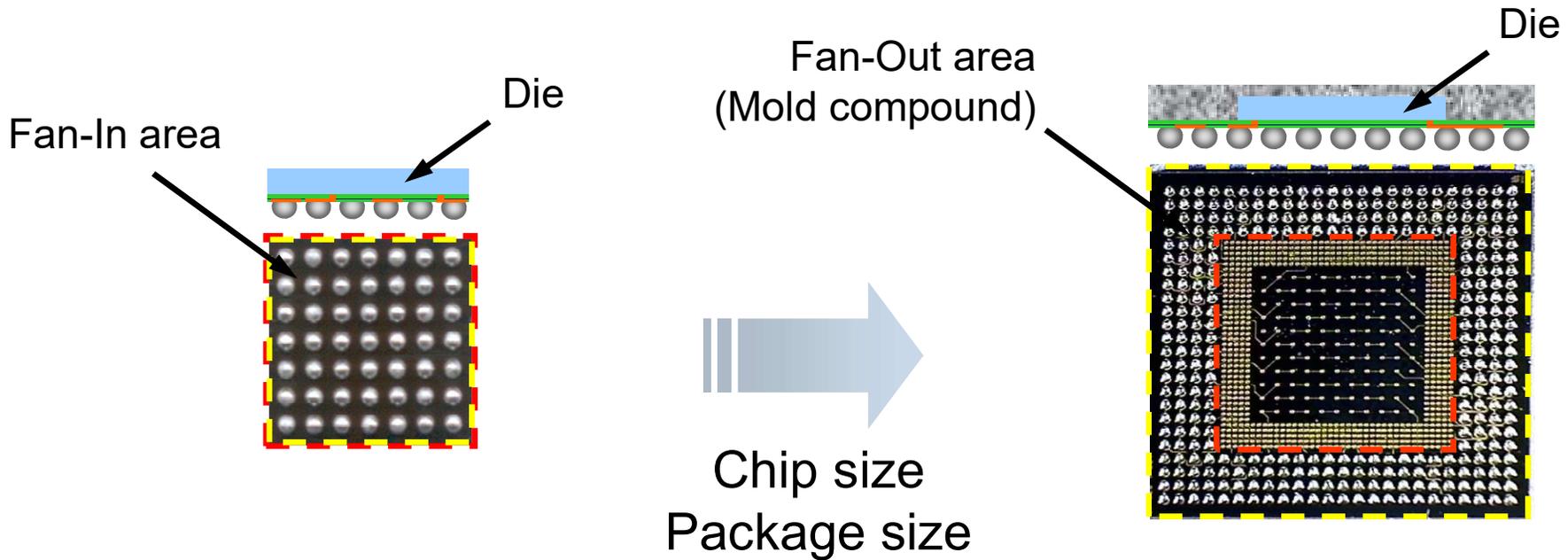
2011
6 GHz CMOS VCO with high-Q fan-out inductors in eWLB

2014
Waveguide integration in eWLB

2013
3D eWLB using TEV Low-loss transitions and high-Q inductors

2015
3D eWLB using EZL Novel concept for vertical interconnection

Embedded Wafer Level BGA (eWLB) Package



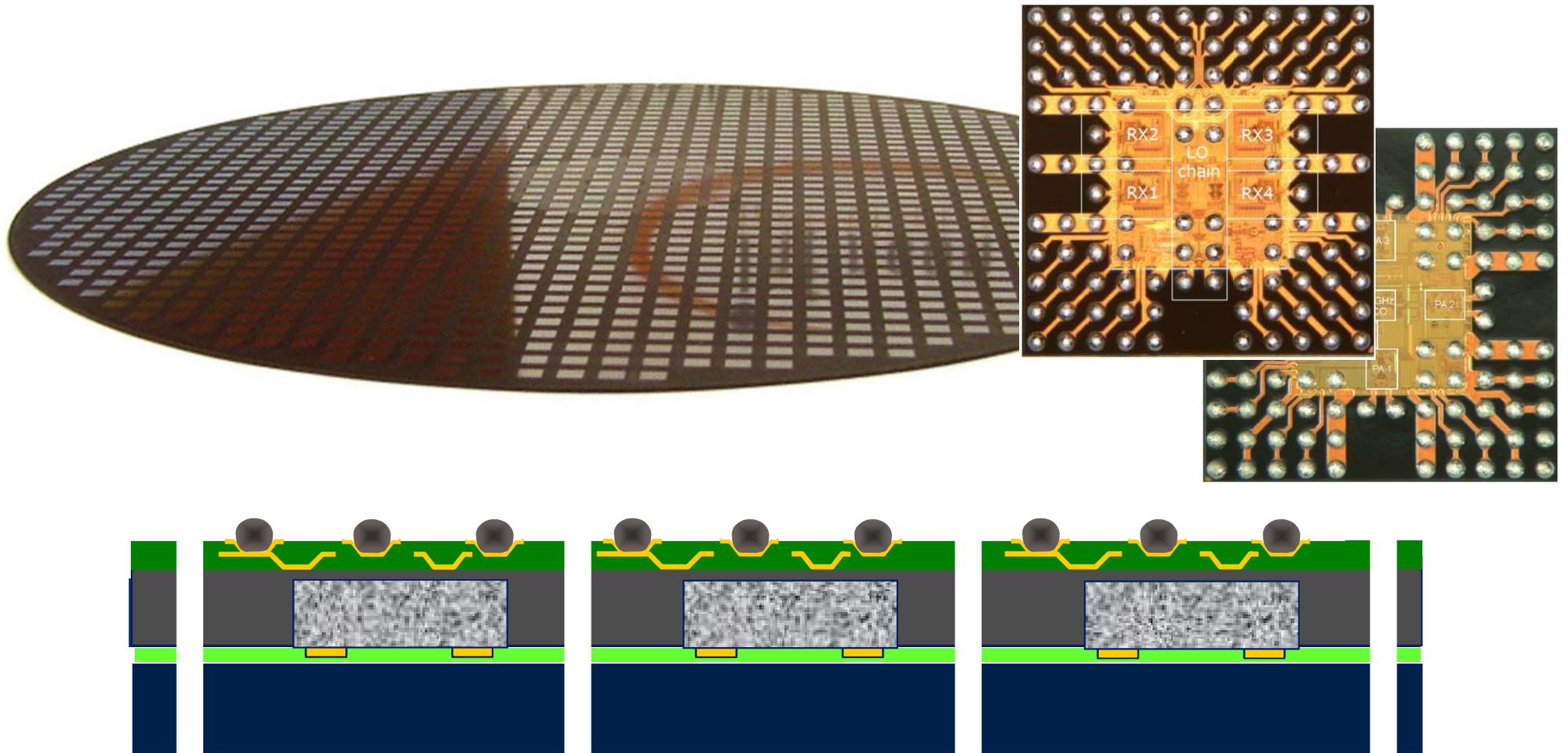
Classical WLB

- All interconnects must fit under the die area
- Number and pitch of interconnects must be adapted to the chip size

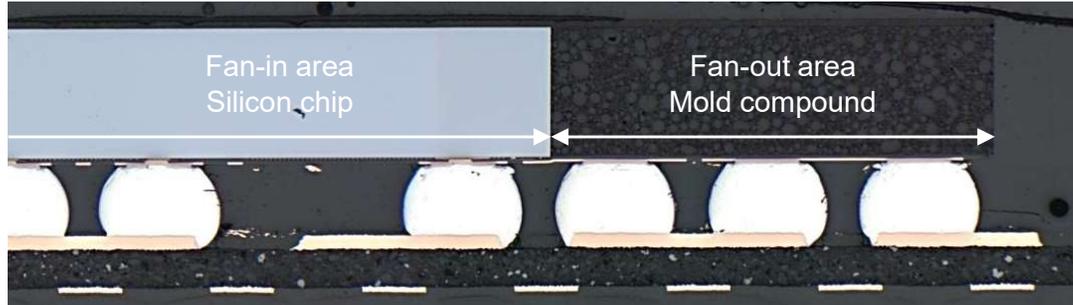
Embedded WLB

- Fan-out area adaptable to needs
- No restrictions for ball pitch

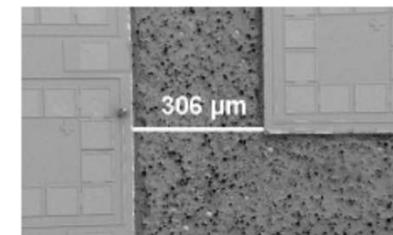
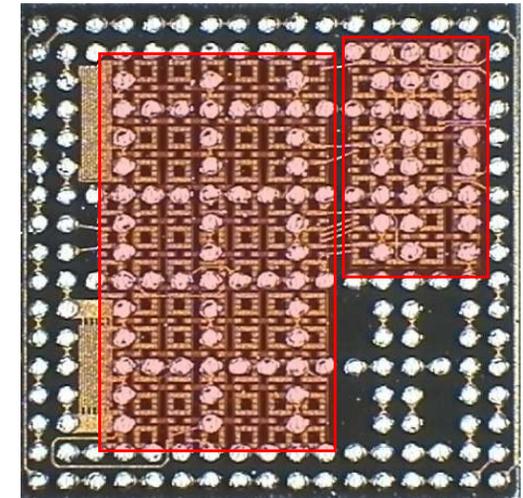
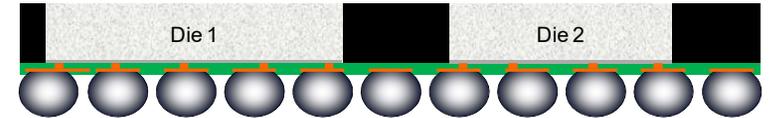
Process Flow for eWLB Package



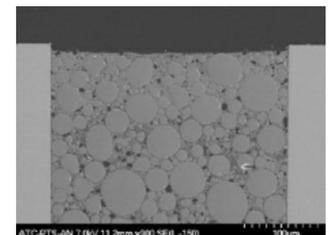
Side-by-Side Integration in eWLB



- Side-by-side integration for multichip modules and passives components e.g. SMD
- Measured loss tangent of mold compound = 0.004 @ 10 GHz and 0.005 @ 80 GHz



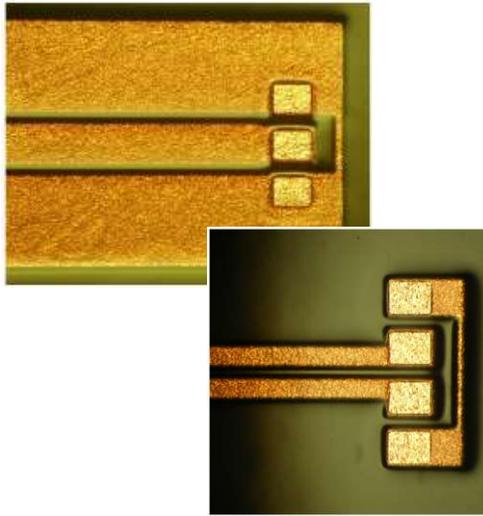
Top view



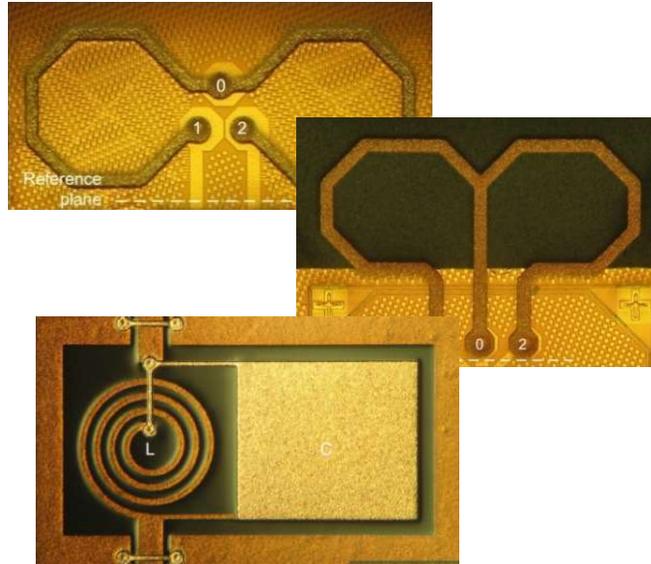
Cross section

Passives Integration in eWLB

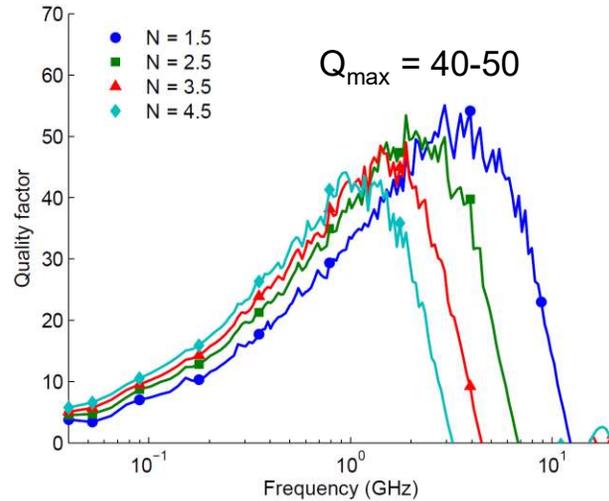
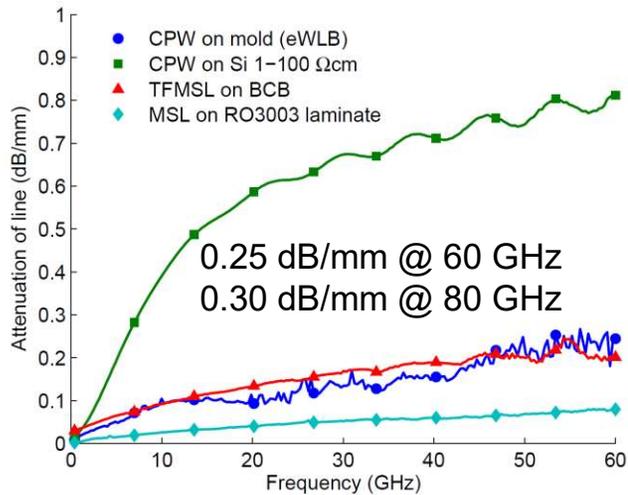
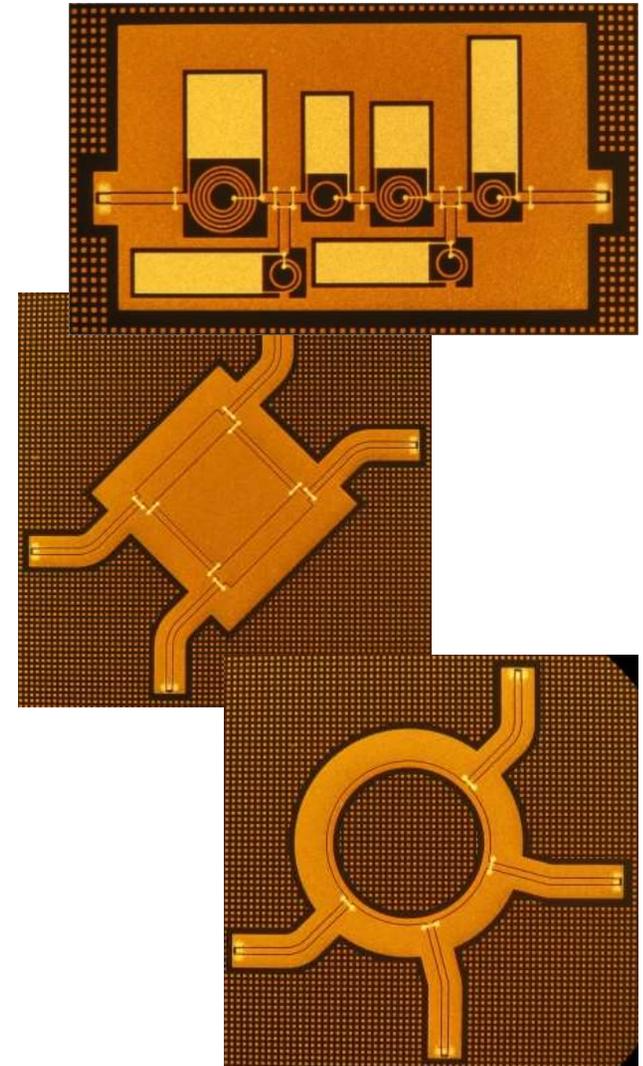
■ Transmission lines



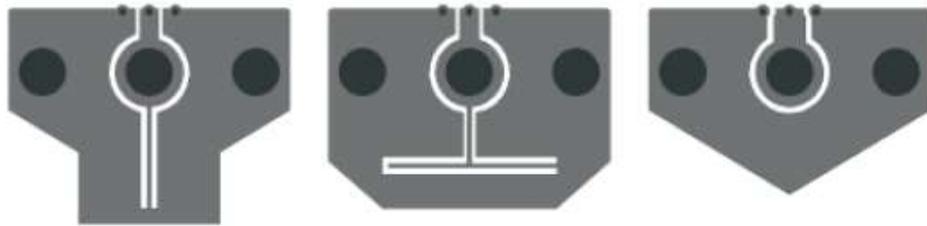
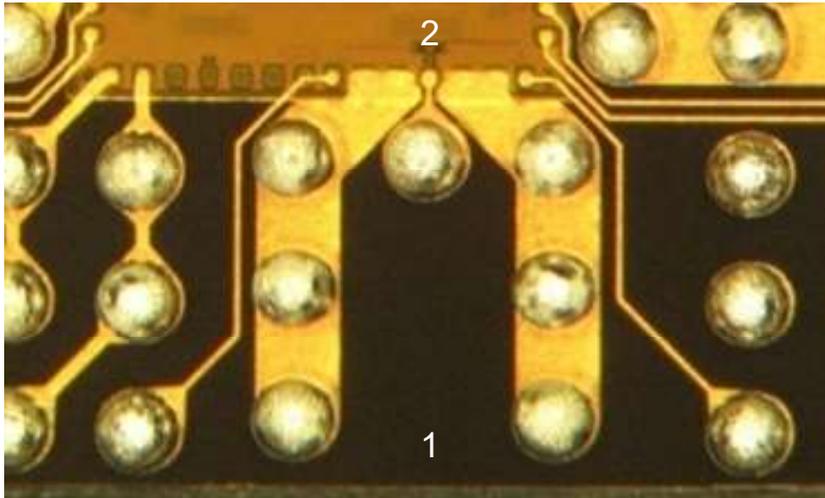
■ Inductors, Capacitors



■ Filters



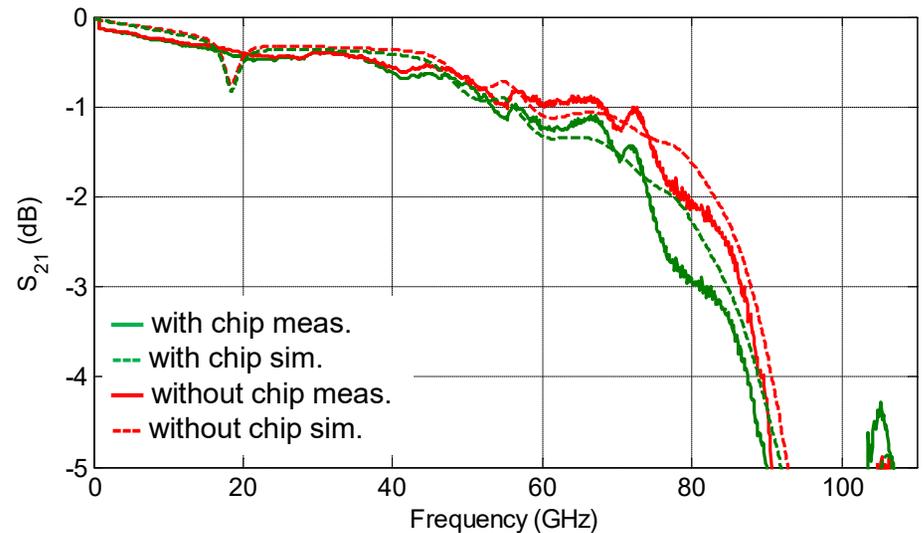
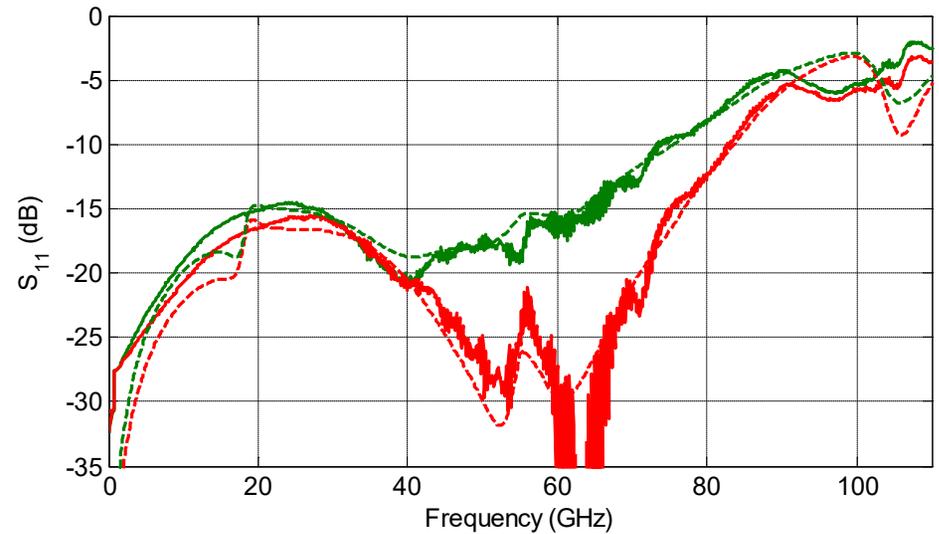
RF Transitions in eWLB



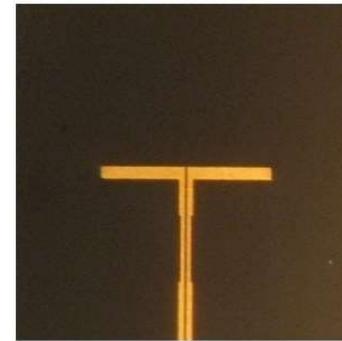
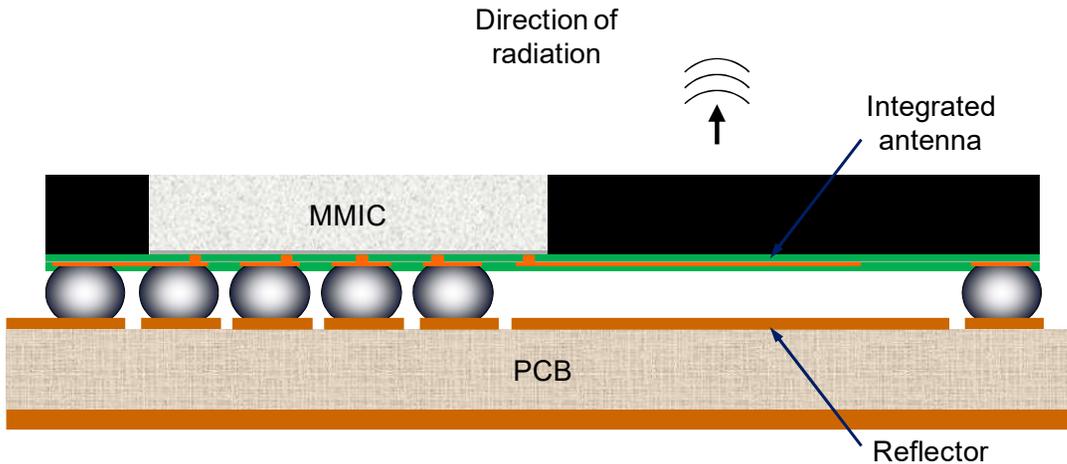
- Performance without external matching at 60 GHz

$$S_{21} = -1.0 \text{ dB}, S_{11} = -15 \text{ dB}$$

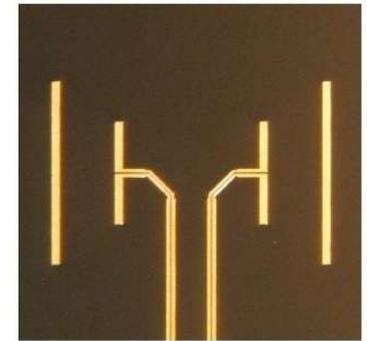
- Broadband and bandpass RF transitions possible using RDL



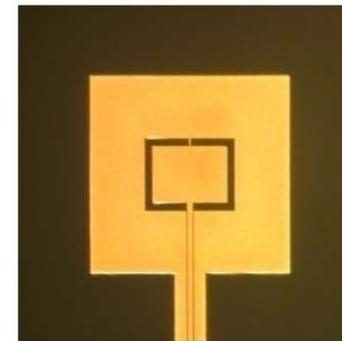
Antenna Integration in eWLB



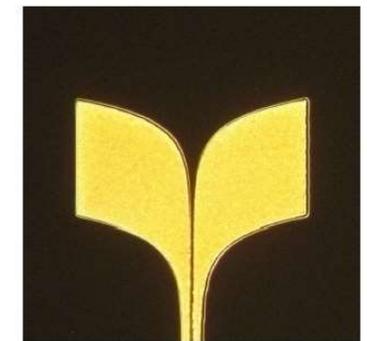
(a) Dipole



(b) Array of two dipoles



(c) CPW patch

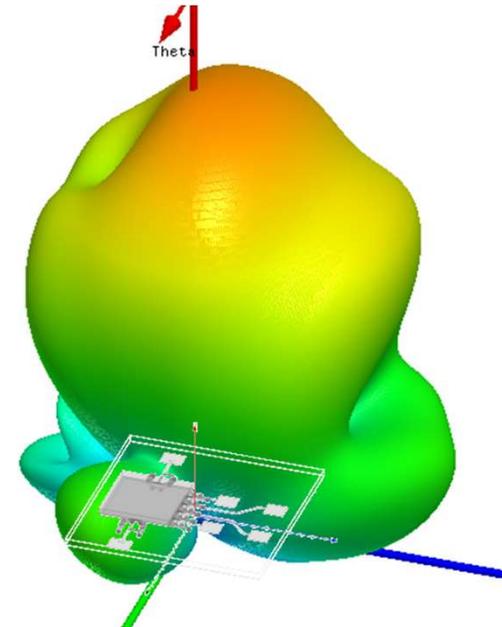
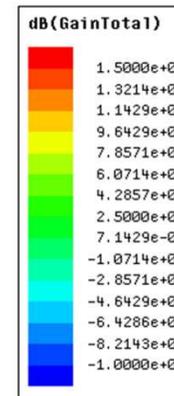
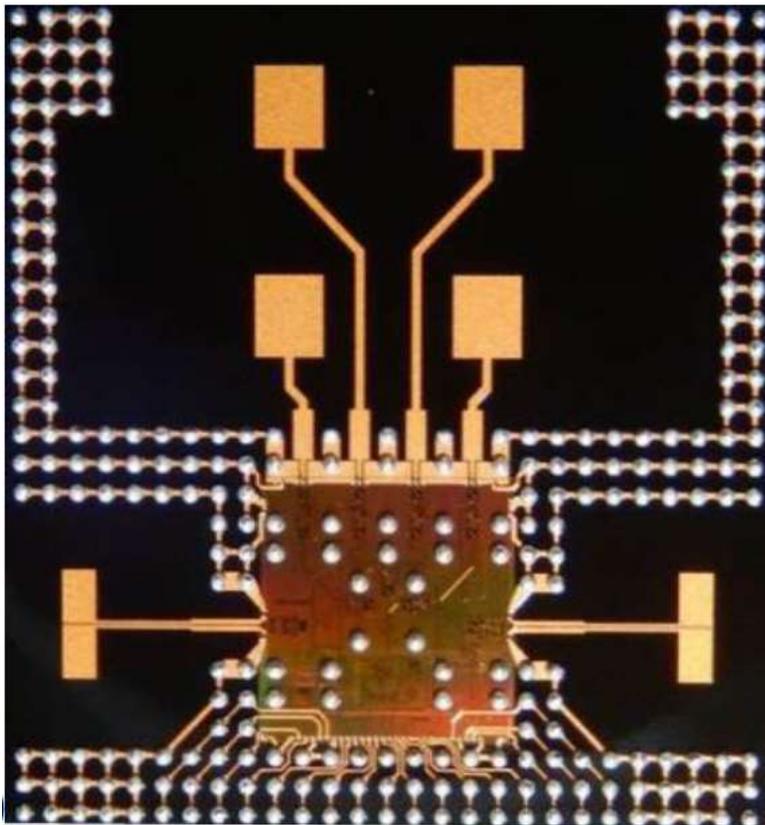


(d) Vivaldi

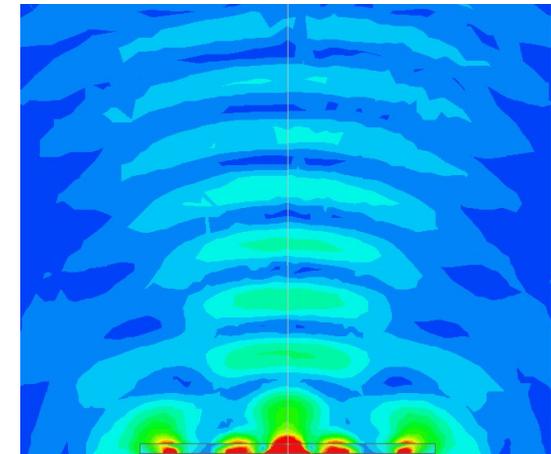
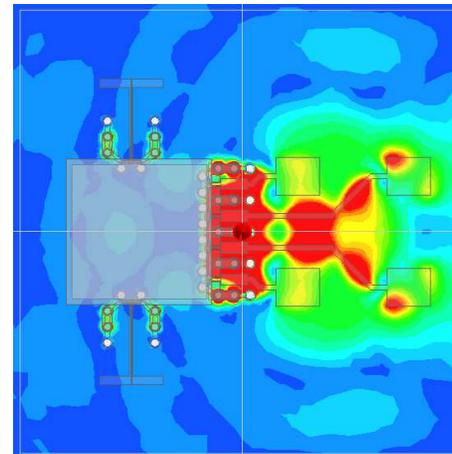
- Antenna realized using RDL in the fan-out area of eWLB
- Plain ground underneath the antenna used as a reflector makes the antenna unconstrained by the actual PCB material

Frequency	λ	Max. antennas	Directivity Nx1	Directivity NxN
40 GHz	7.50 mm	3x3	11.3 dBi	14.6 dBi
60 GHz	5.00 mm	4x4	13.0 dBi	18.1 dBi
80 GHz	3.75 mm	5x5	14.3 dBi	20.6 dBi
100 GHz	3.00 mm	6x6	15.3 dBi	22.5 dBi
120 GHz	2.50 mm	7x7	16.0 dBi	24.1 dBi

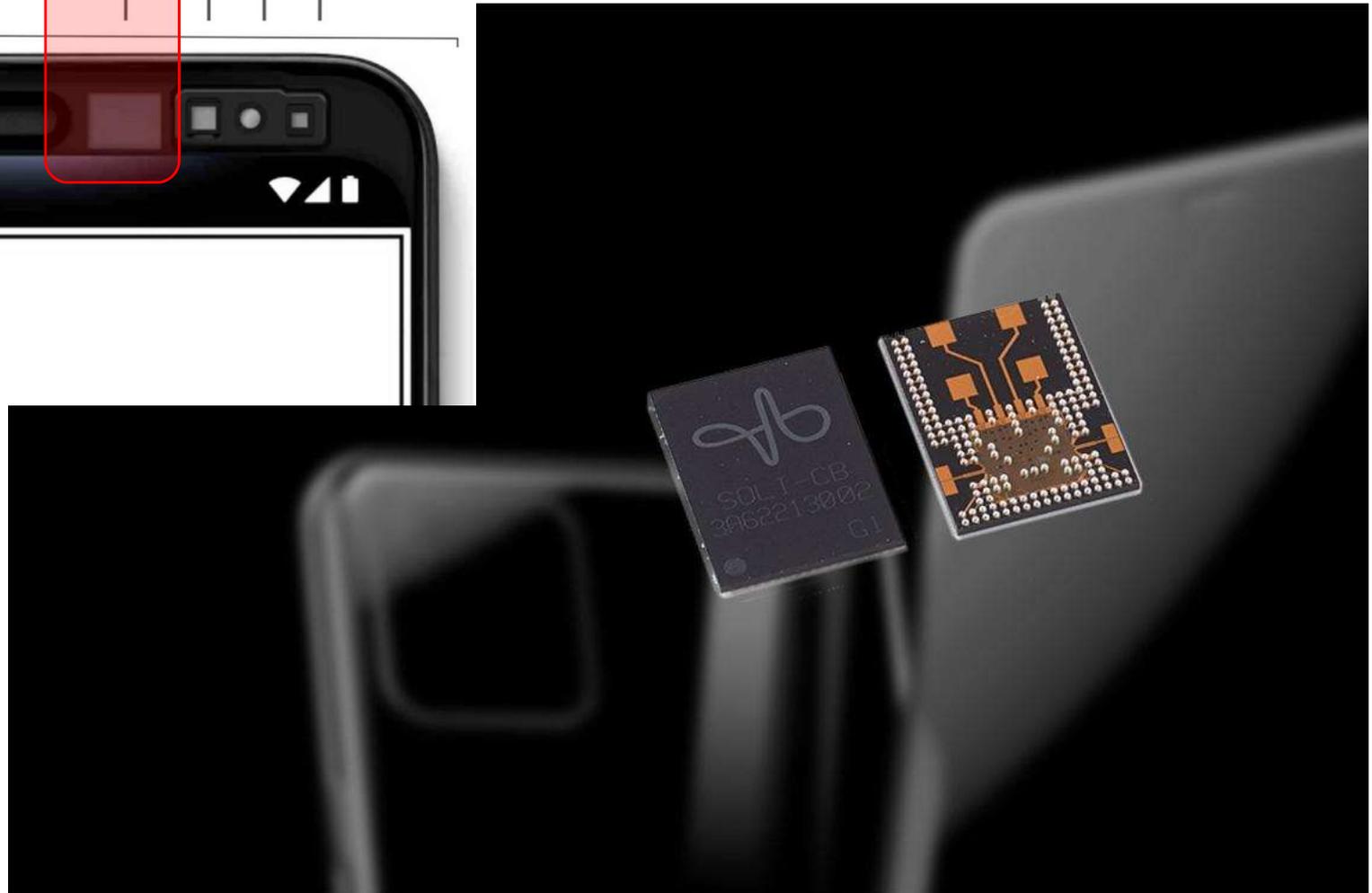
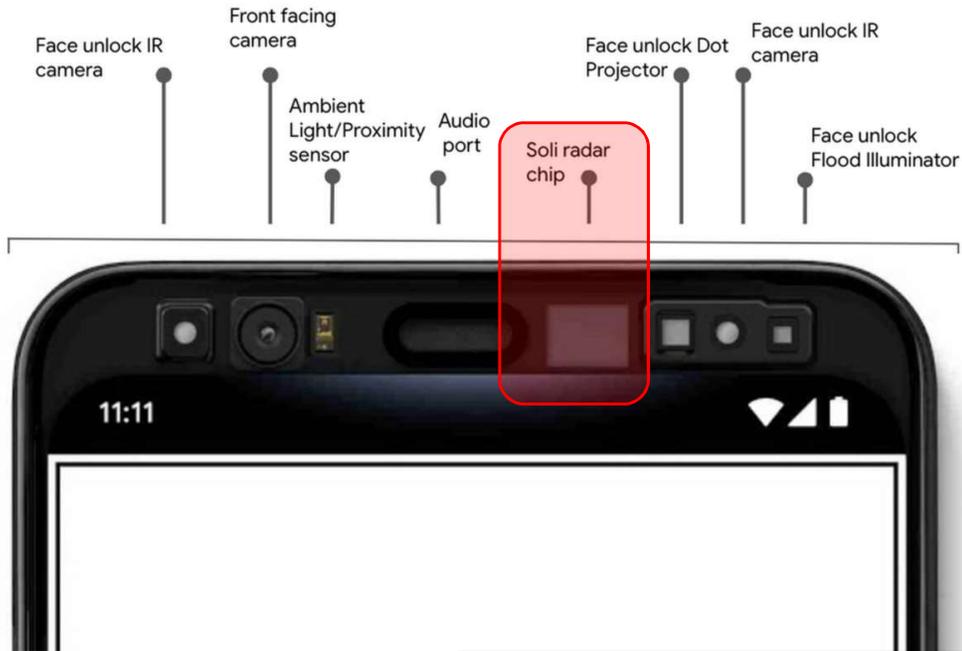
60 GHz 6-Channel Transceiver Module in eWLB



- 14 mm x 14 mm eWLB package
- 4xRX patch antennas and 2xTX dipole antennas



Google's Pixel 4 Worldwide First Radar Sensor in a Smartphone

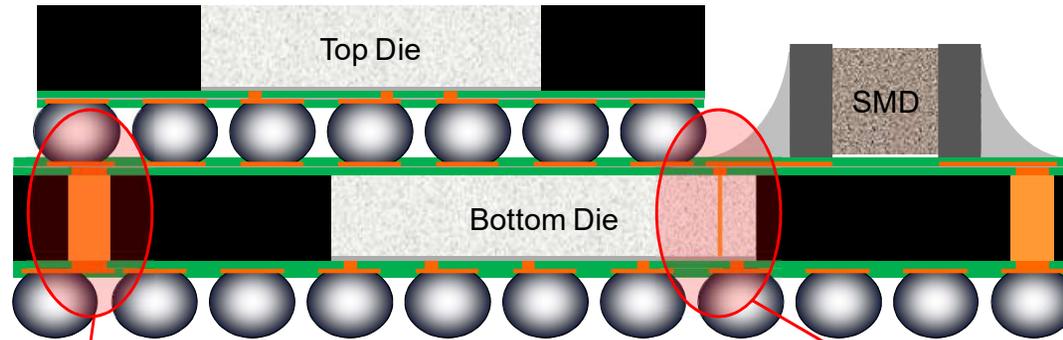


Agenda

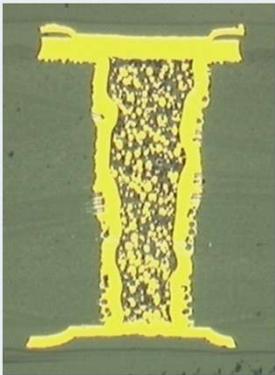
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Vertical Interconnections in 3D eWLB

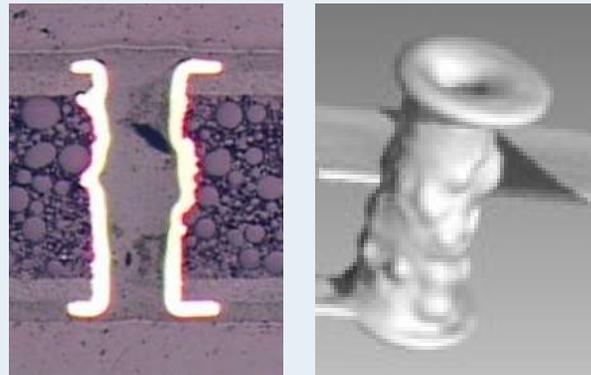
3D eWLB



Embedded via bar

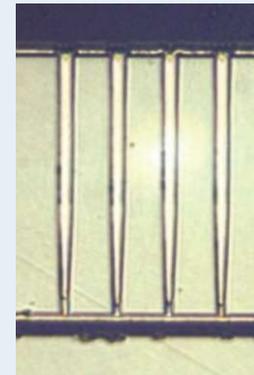


Thru encapsulant via (TEV)



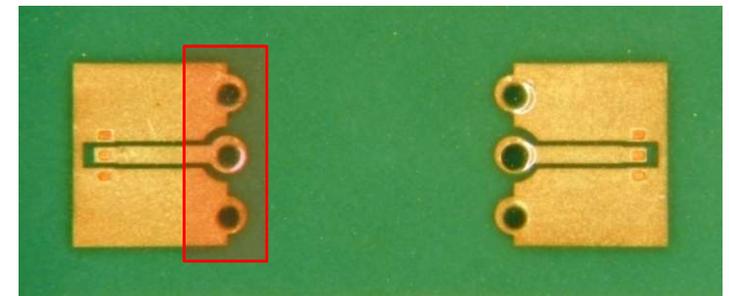
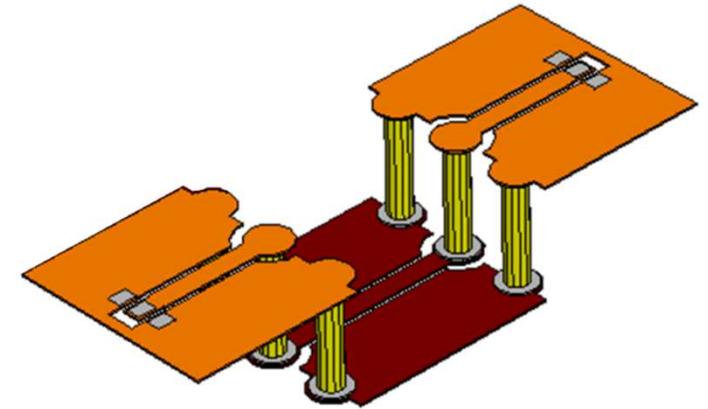
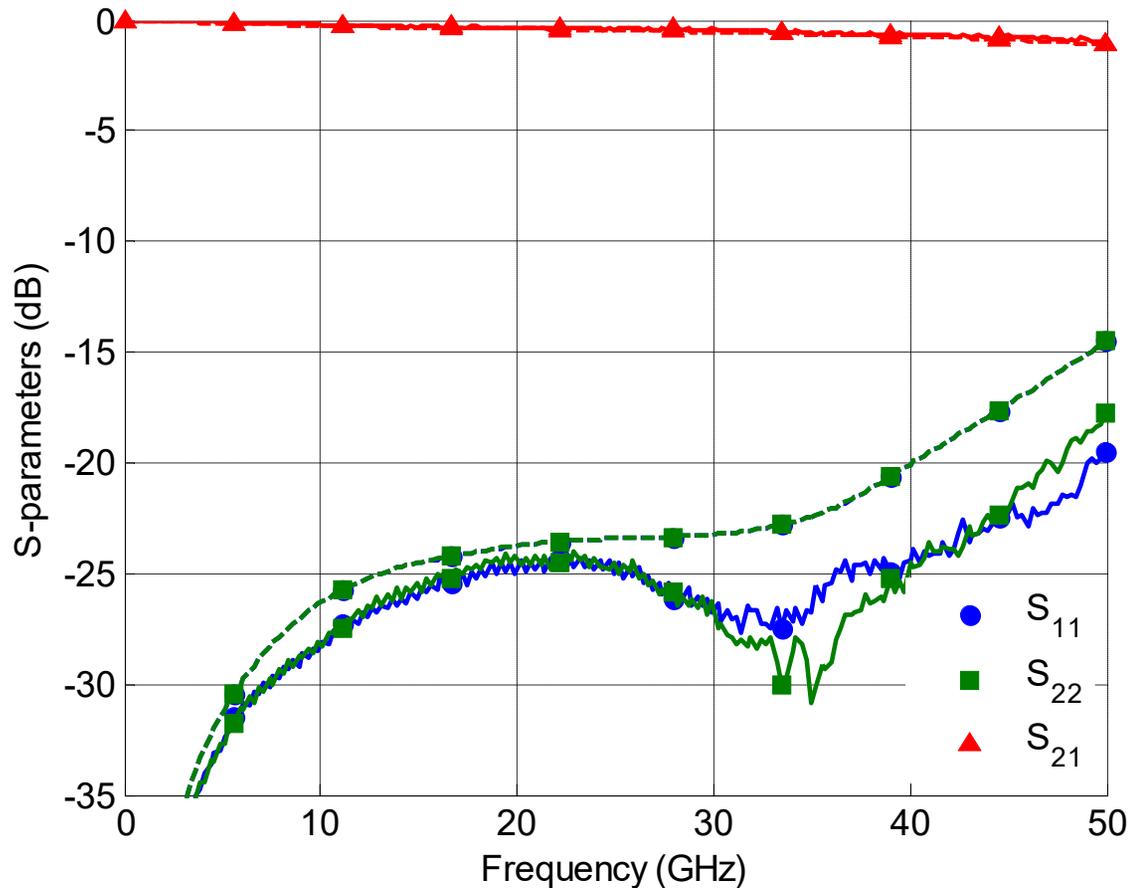
- Diameter = 200 μm
- Depth = 300 μm
- Pitch = 300 μm

Thru silicon via (TSV)



- Diameter = 10 μm
- Depth = 75 μm
- Pitch = 50 μm

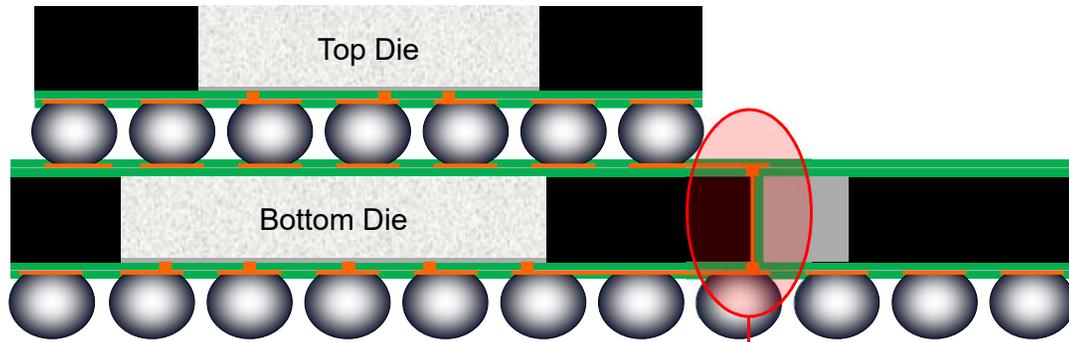
Vertical RF Transitions Using TEV



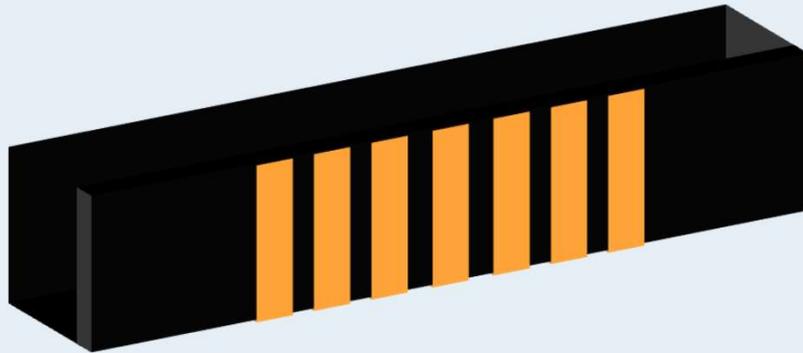
- Measured back-to-back connection of two GSG vertical transition realized using TEV in eWLB
- RF performance up to 50 GHz $S_{21} < 1$ dB, $S_{11}, S_{22} < -15$ dB

Embedded Z Line (EZL) Concept

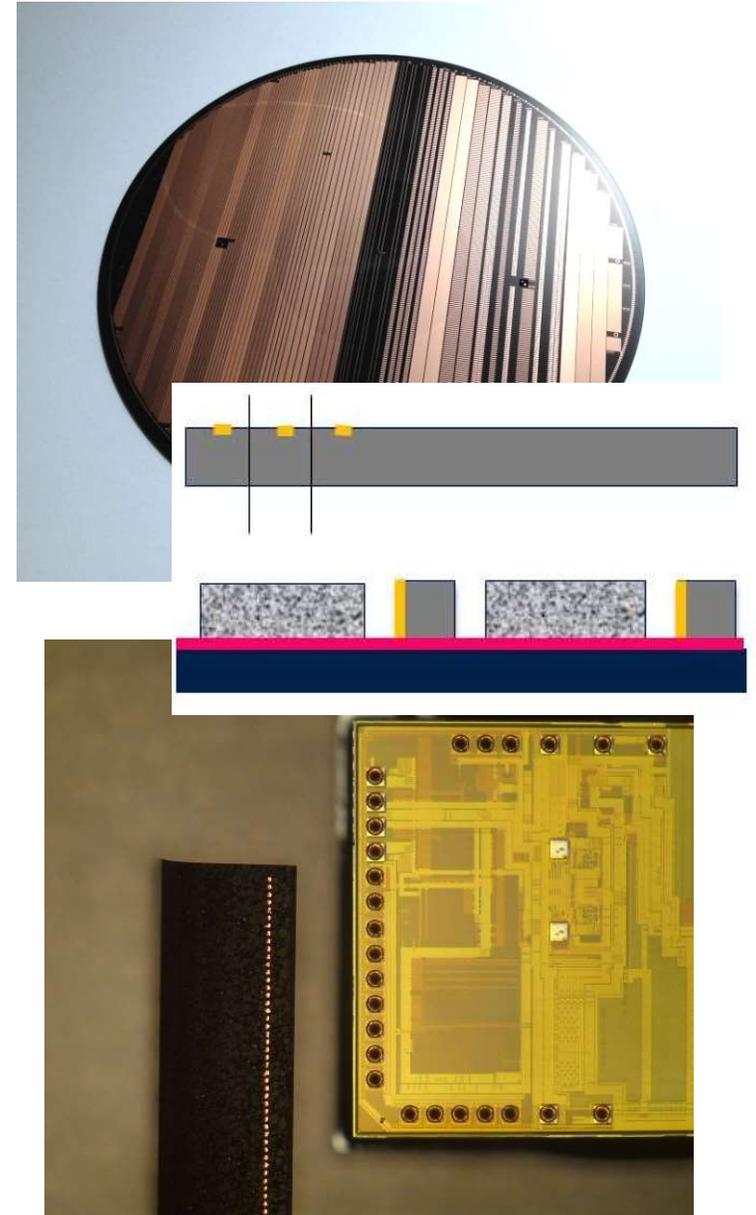
3D eWLB



Embedded Z Line (EZL)



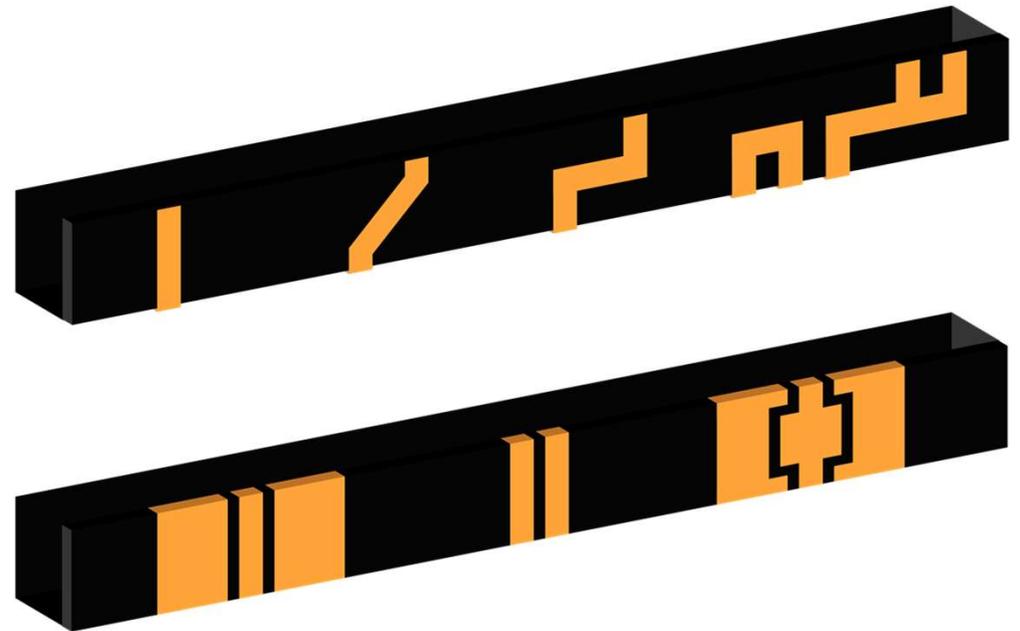
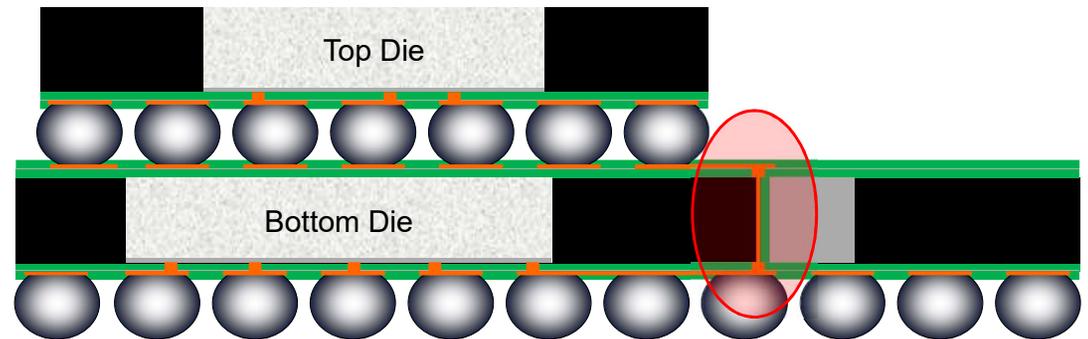
- EZLs are pre-fabricated bricks of mold compound turned by 90° with interconnections realized using RDL



Embedded Z Line (EZL) Concept

Advantages of horizontal RDL

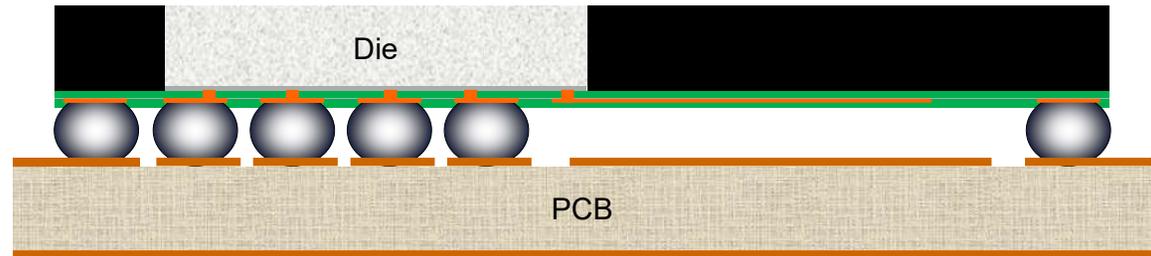
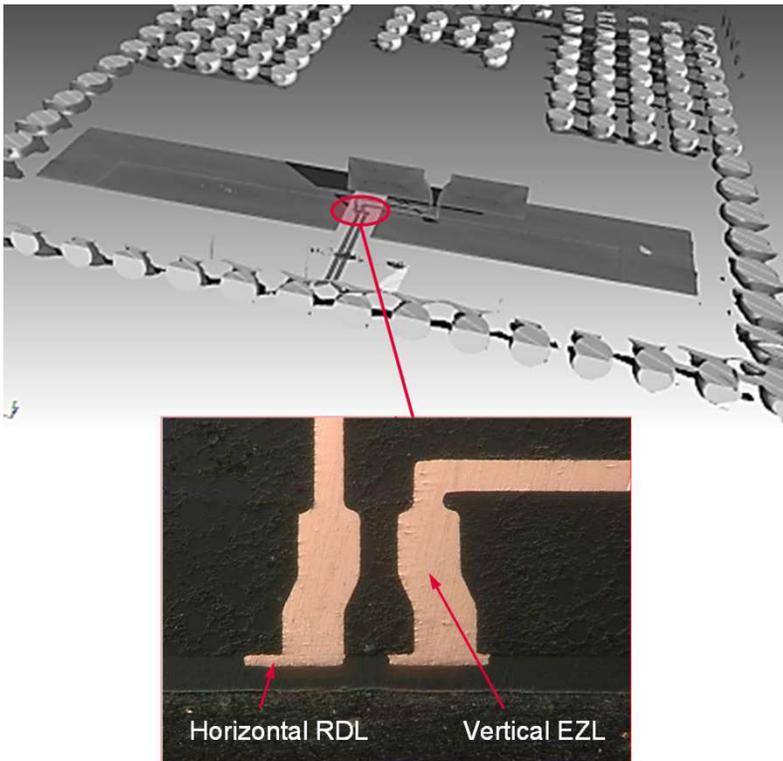
- High metal-pattern resolution
- Wide range of widths and pitches from few up to hundreds of μm
- Non-uniform cross section
 - Skewed, stepwise interconnections
 - Complex signal/power distribution networks
 - Transmission lines and matching networks



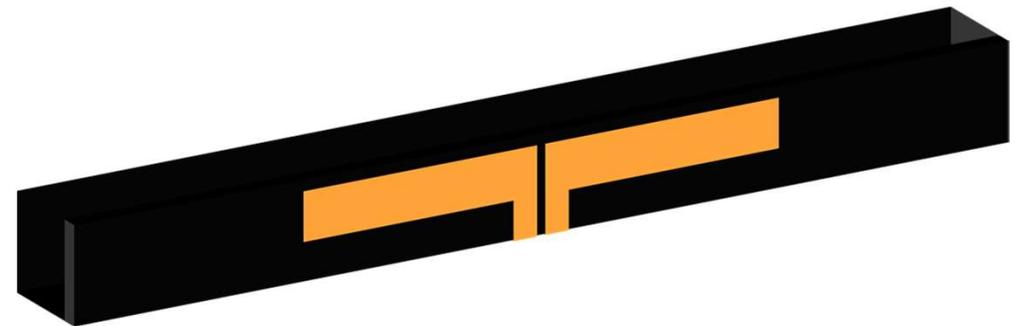
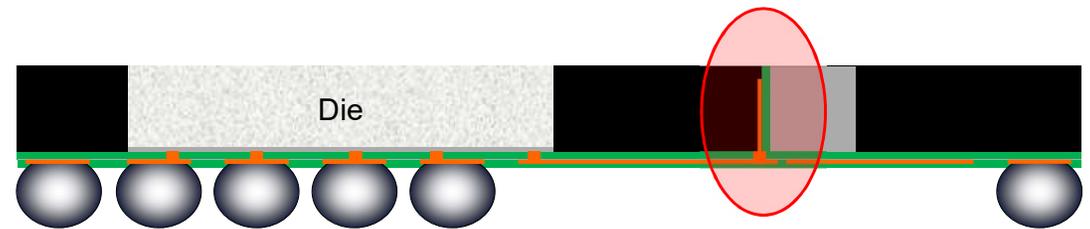
Vertical Dipole Antenna using EZL

EZL antenna

- Reflector realized using the horizontal RDL
- More compact and less sensitive to assembly tolerances



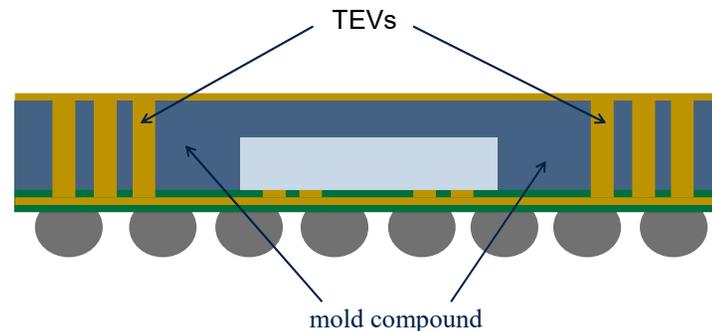
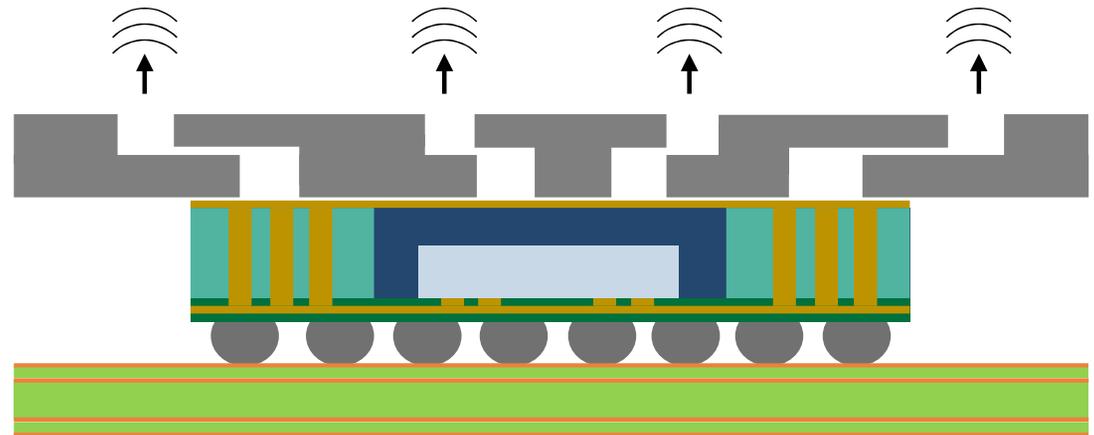
Traditional antenna integration using RDL



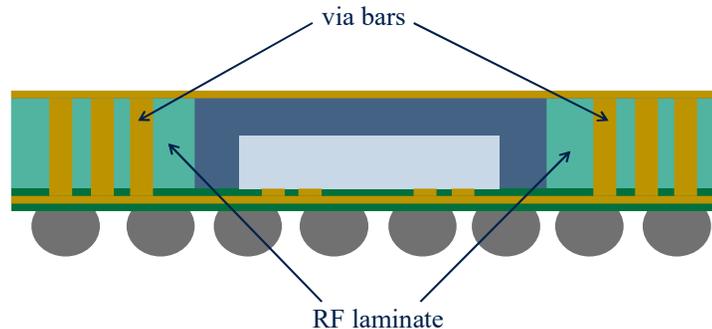
New antenna integration using EZL

Substrate Integrated Waveguide (SIW) in eWLB

- Rectangular waveguides offer the lowest transmission losses
- Substrate integrated waveguide (SIW) in eWLB
 - Propagation characteristics of travelling waves similar to those of rectangular waveguides
 - Sidewalls created with vias
 - Propagation mode TE_{10}
 - Radiation and leakage can be neglected



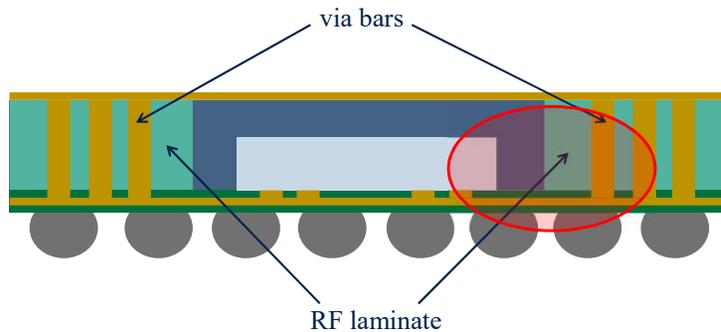
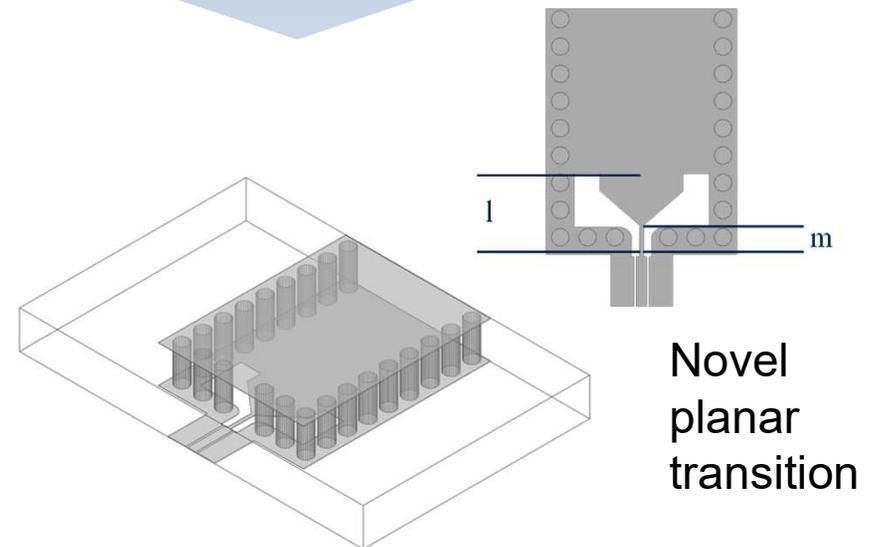
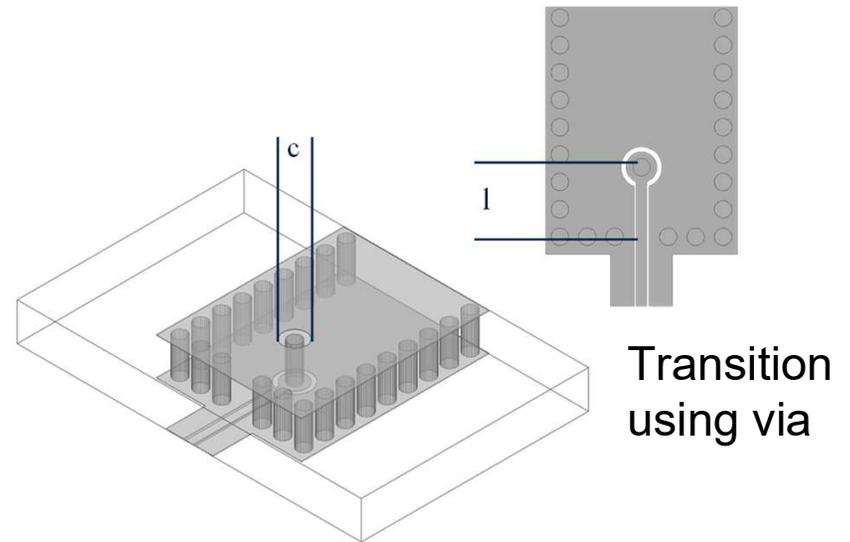
Sidewalls realized using TEVs



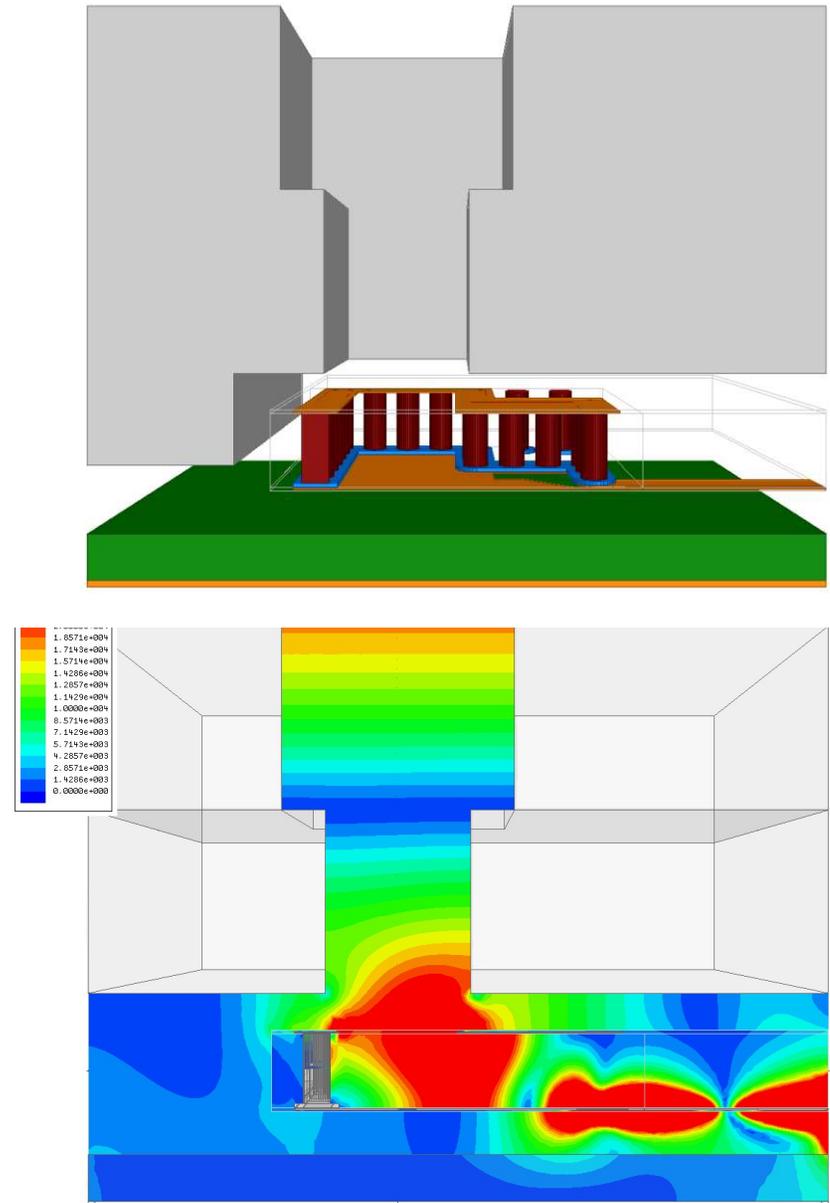
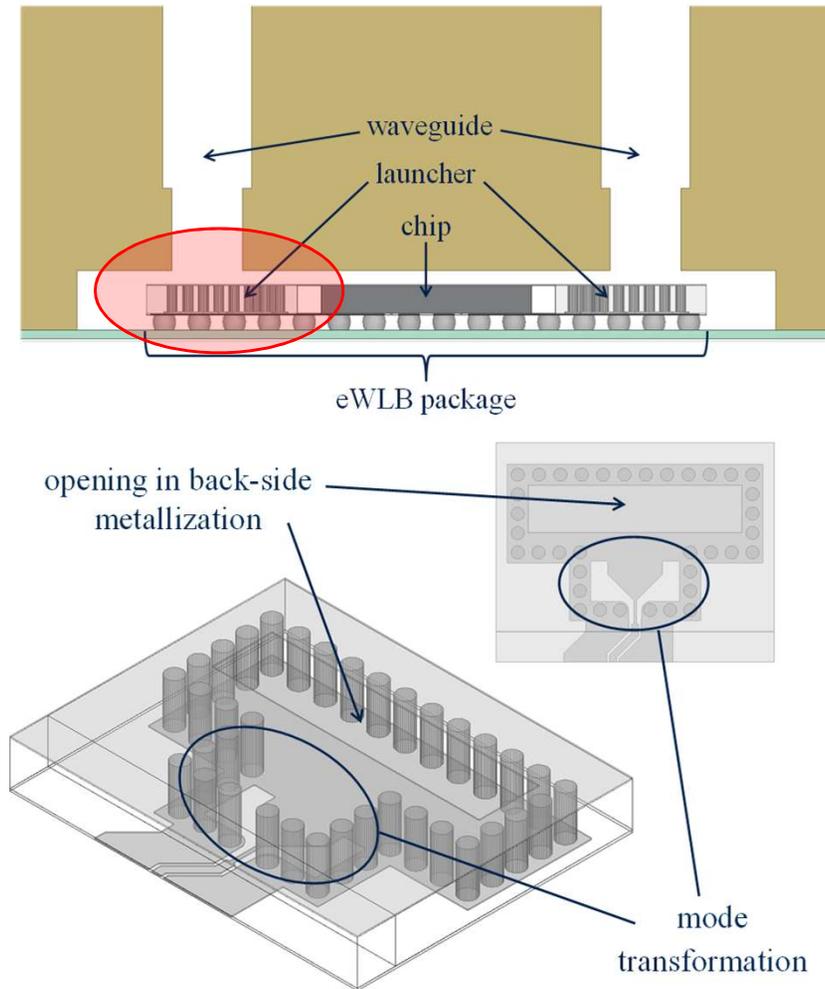
Sidewalls realized using via bars

Chip-SIW Transition in eWLB

- Transition needs to realize mode conversion from CPW to TE_{10} mode
- Novel fully planar transition using taper
 - Broadband matching by shaping the taper
 - More degrees of freedom for layout and optimization
 - Reduced impact of tolerances

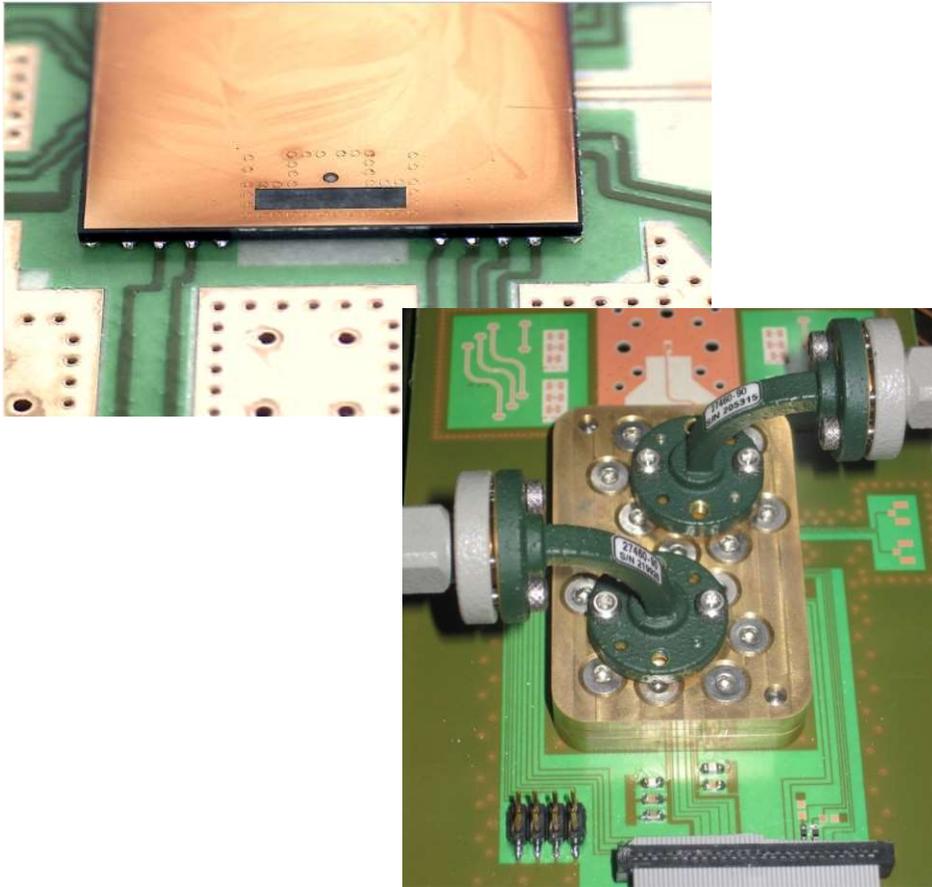


Chip-Package-WR10 Waveguide Transition in eWLB

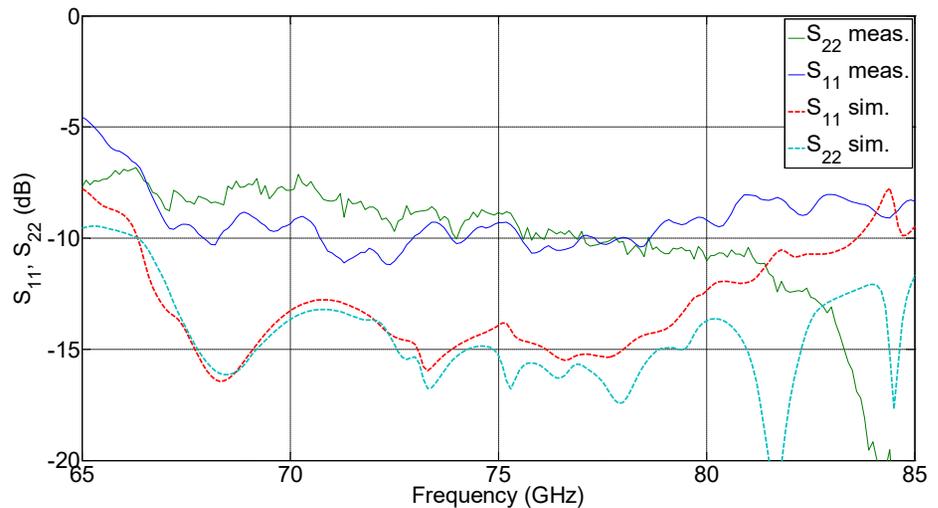
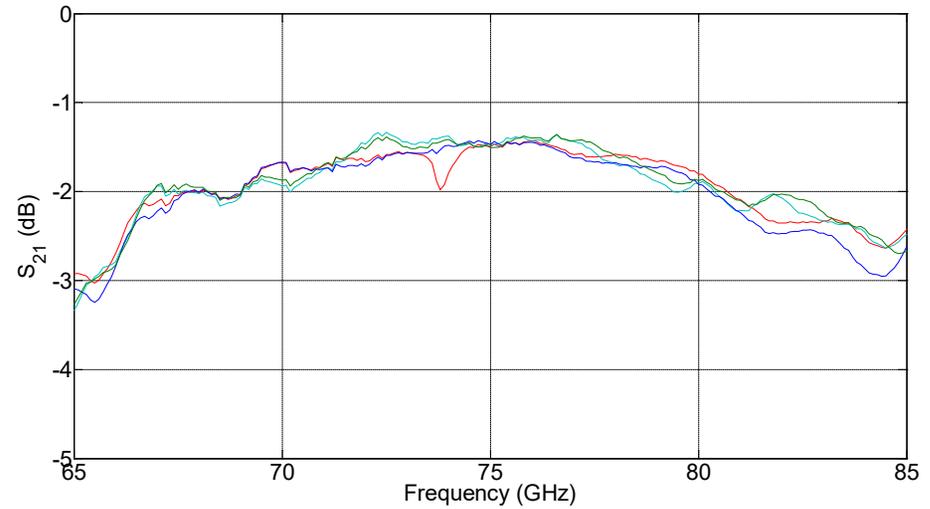


- Compact low-loss chip-package-WR-10 waveguide RF transition in eWLB realized using taper

Chip-Package-WR10 Waveguide Transition in eWLB



Transition using taper



■ Measured and simulated chip-WR10 transition using taper

■ Performance at 77 GHz

$$S_{21} = -1.5 \text{ dB}, S_{11}, S_{22} < -10 \text{ dB}$$

Agenda

- 1 Introduction
- 2 Millimeter-Wave System Integration
- 3 2D Embedded Wafer Level BGA (eWLB)
- 4 3D System Integration Applying eWLB
- 5 Summary

Summary

- More than Moore trend pushes packaging development **toward system-in-package**
- System design at mm-waves requires new methodologies for **coherent chip-package-board co-design**
- Embedded wafer level BGA (eWLB) is a **universal SiP integration platform for RF/mm-wave applications**
 - High I/O and interconnect density
 - Outstanding RF/mm-wave performance
 - Outstanding flexibility for 2D/3D system integration: multichip, embedded passives, antenna and waveguide

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